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PMN50UPE

20 V, single P-channel Trench MOSFET

20 July 2012

Product data sheet

1. Product profile

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- 3 kV ESD protected
- Trench MOSFET technology
- Low threshold voltage

1.3 Applications

- · Relay driver
- High-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V_{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	-4	Α
Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -3.6 A; T_j = 25 °C		-	50	66	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².





20 V, single P-channel Trench MOSFET

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	<u> </u>	D I
2	D	drain		
3	G	gate		$G \left(\begin{array}{c} \overline{A} \end{array} \right)$
4	S	source	TSOP6 (SOT457)	
5	D	drain		
6	D	drain		S 017aaa259

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMN50UPE	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457

4. Marking

Table 4. Marking codes

Type number	Marking code
PMN50UPE	WH

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V_{GS}	gate-source voltage			-8	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-4	Α
		V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-3.6	Α
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-2.3	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs		-	-14.4	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	<u>[2]</u>	-	510	mW
			[1]	-	1235	mW
		T _{sp} = 25 °C		-	5000	mW

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Symbol	Parameter	Conditions		Min	Max	Unit
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain of	diode		,			
I _S	source current	T _{amb} = 25 °C	[1]	-	-1.3	Α
ESD maximum rating						
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	3000	V

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

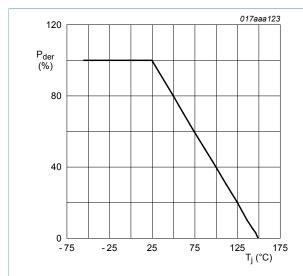


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

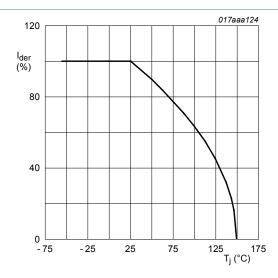


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

20 V, single P-channel Trench MOSFET

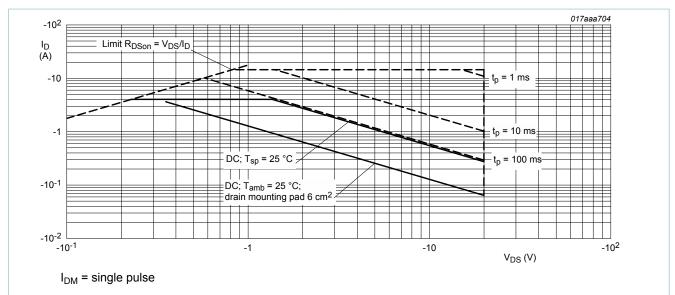


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient			[1]	-	213	245	K/W
	-		[2]	-	88	100	K/W
	ambient		[3]	-	70	81	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	21	25	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm², $t \le 5$ s.

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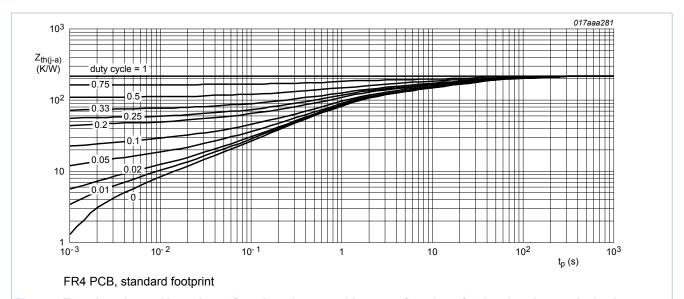


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

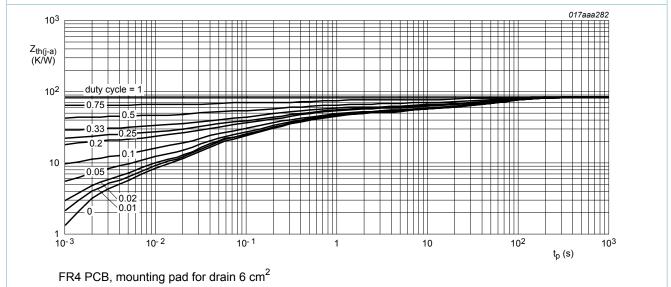


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = -250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C	-0.47	-0.6	-0.9	V
I _{DSS}	drain leakage current	V_{DS} = -20 V; V_{GS} = 0 V; T_j = 25 °C	-	-	-1	μA
		V _{DS} = -20 V; V _{GS} = 0 V; T _j = 150 °C	-	-	-10	μΑ
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Symbol	Parameter	Conditions	Mi	n Typ	Max	Unit
I _{GSS}	gate leakage current	$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	10	μA
		V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
R _{DSon}	drain-source on-state	V_{GS} = -4.5 V; I_{D} = -3.6 A; T_{j} = 25 °C	-	50	66	mΩ
	resistance	V_{GS} = -4.5 V; I_D = -3.6 A; T_j = 150 °C	-	73	96	mΩ
		V_{GS} = -2.5 V; I_D = -2.1 A; T_j = 25 °C	-	57	81	mΩ
		V_{GS} = -1.8 V; I_D = -2.1 A; T_j = 25 °C	-	70	110	mΩ
9fs	forward transconductance	V_{DS} = -5 V; I_{D} = -3.6 A; T_{j} = 25 °C	-	18	-	S
Dynamic cl	naracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I_{D} = -3.2 A; V_{GS} = -4.5 V;	-	10.5	15.7	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	2.2	-	nC
Q_{GD}	gate-drain charge		-	2.7	-	nC
C _{iss}	input capacitance	V_{DS} = -10 V; f = 1 MHz; V_{GS} = 0 V;	-	24	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	106	-	pF
C _{rss}	reverse transfer capacitance		-	14.6	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I_{D} = -3.6 A; V_{GS} = -4.5 V;	-	400	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	700	-	ns
t _{d(off)}	turn-off delay time		-	2180	-	ns
t _f	fall time		-	8800	-	ns
Source-dra	in diode	-1	1	1	1	
V _{SD}	source-drain voltage	I _S = -1.3 A; V _{GS} = 0 V; T _j = 25 °C	-	-0.8	-1.2	V

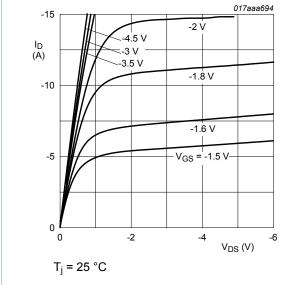


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

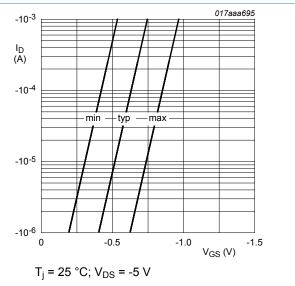


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

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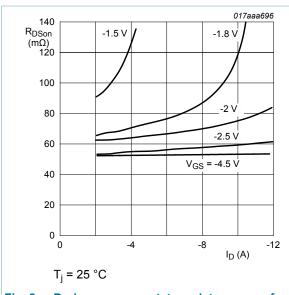


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

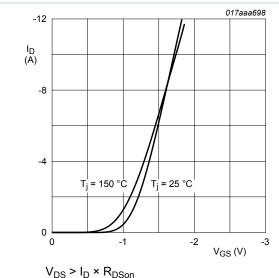


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

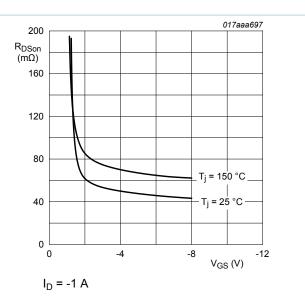


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

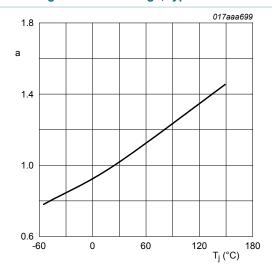


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

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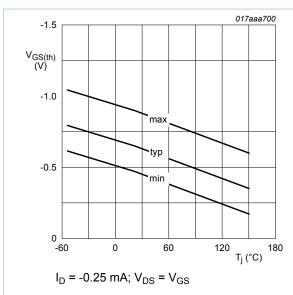


Fig. 12. Gate-source threshold voltage as a function of junction temperature

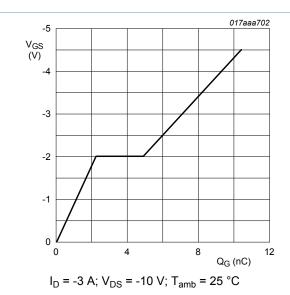


Fig. 14. Gate-source voltage as a function of gate charge; typical values

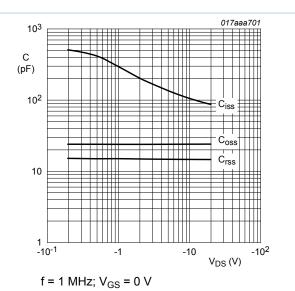


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

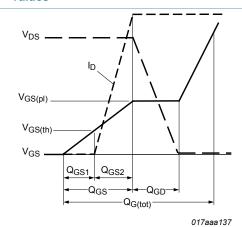
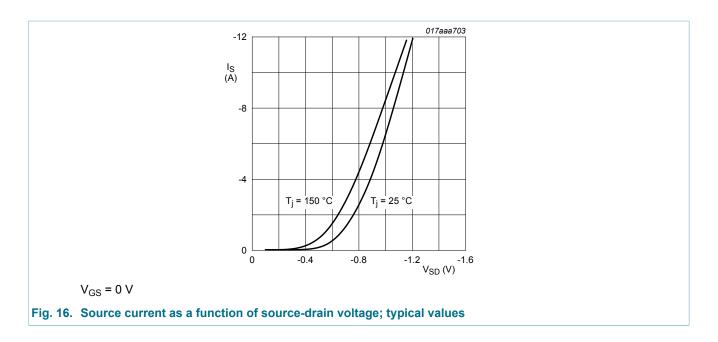
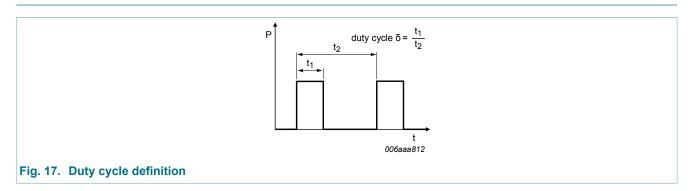


Fig. 15. Gate charge waveform definitions

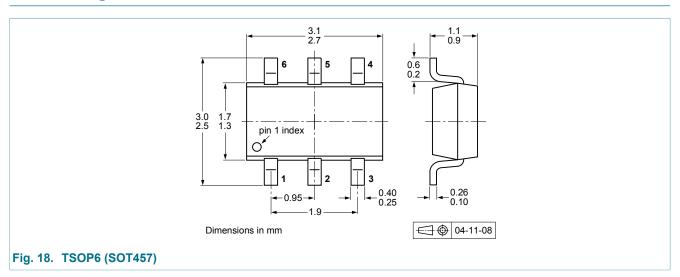
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8. Test information



9. Package outline

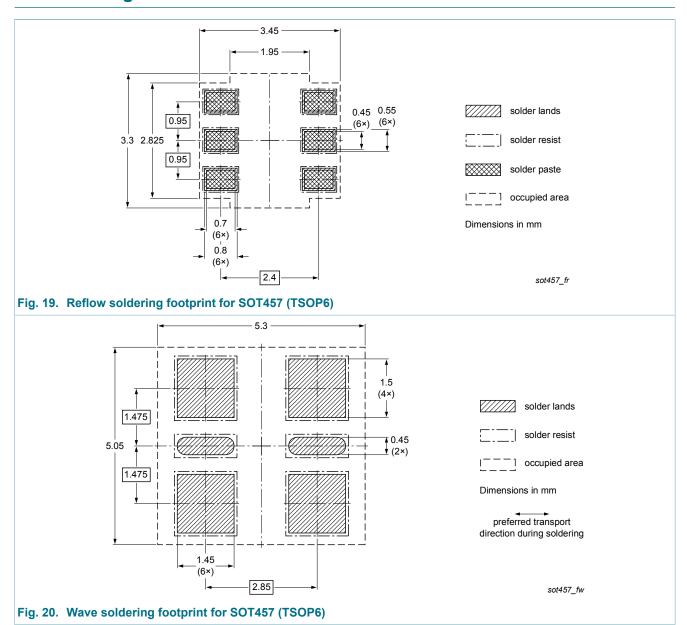


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10. Soldering



11. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMN50UPE v.1	20120720	Product data sheet	-	-

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Document status [1][2]	Product status [3]	Definition
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